

## DESCRIPTION

This new series of digital transistors is designed to replace a single device and its external resistor bias network. The BRT (Bias Resistor Transistor) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base-emitter resistor. The BRT eliminates these individual components by integrating them into a single device. The use of a BRT can reduce both system cost and board space. The device is housed in the SC-89 package which is designed for low power surface mount applications.

The DTC114EE~DTC144WE is available in SC-89 Package

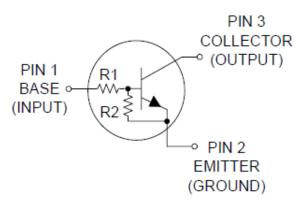
### **ORDERING INFORMATION**

Package Type	Part Number			
	DTC114EE			
	DTC124EE			
	DTC144EE			
	DTC114YE			
	DTC114TE			
SC-89	DTC143TE			
	DTC123EE			
	DTC143EE			
	DTC143ZE			
	DTC124XE			
	DTC123JE			
	DTC115EE			
	DTC144WE			
Note	SPQ: 3,000pcs/Reel			
AiT provides all RoHS Compliant Products				

## FEATURES

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- The SC-89 package can be soldered using wave or reflow. The modified gull-winged leads absorb thermal stress during soldering eliminating the possibility of damage to the die.
- Available in SC-89 Package

## PIN DESCRIPTION





BIAS RESISTOR TRANSISTORS NPN SILICON WITH MONOLITHIC BIAS RESISTOR NETWORK

## ABSOLUTE MAXIMUM RATINGS

#### $T_A = 25^{\circ}C$ , unless otherwise noted

V <sub>CBO</sub> , Collector-Base Voltage	50Vdc
V <sub>CEO</sub> , Collector-Emitter Voltage	50Vdc
I <sub>C</sub> , Collector Current	100mAdc

Stresses above may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated in the Electrical Characteristics are not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

## THERMAL CHARACTERISTICS

Parameter	Symbol	Value	Unit
Total Device Dissipation, FR-4 Board NOTE1			
@ T <sub>A</sub> = 25°C	PD	200	mW
Derate above 25°C		1.6	mW/°C
Thermal Resistance, Junction-to-Ambient NOTE1	Reja	600	°C/W
Total Device Dissipation, FR-4 Board NOTE2			
@ T <sub>A</sub> = 25°C	PD	300	mW
Derate above 25°C		2.4	mW/°C
Thermal Resistance, Junction-to-Ambient NOTE2	Reja	400	°C/W
Junction and Storage Temperature Range	Tj, Tstg	−55 to +150	°C

NOTE1: FR-4 @ Minimum Pad

NOTE2: FR-4 @ 1.0 × 1.0 Inch Pad



# ELECTRICAL CHARACTERISTICS

 $T_A$  = 25°C, unless otherwise noted

Parameter	Symbol	Conditio	ns	Min.	Тур.	Max.	Unit
OFF CHARACTERISTICS							
Collector-Base Cutoff Current	Ісво	V <sub>CB</sub> = 50 V, I <sub>E</sub> = 0				100	nAdc
Collector-Emitter Cutoff Current	ICEO	V <sub>CE</sub> = 50 V, I <sub>B</sub> = 0				500	nAdc
			DTC114EE			0.5	
			DTC124EE			0.2	
			DTC144EE			0.1	
			DTC114YE			0.2	
			DTC114TE			0.9	
			DTC143TE			1.9	
Emitter-Base Cutoff Current	I <sub>EBO</sub>	$V_{EB}$ = 6.0 V, I <sub>C</sub> = 0	DTC123EE			2.3	mAdc
			DTC143EE			1.5	
			DTC143ZE			0.18	
			DTC124XE			0.13	
			DTC123JE			0.2	
			DTC115EE			0.05	
			DTC144WE			0.13	
Collector-Base Breakdown	V <sub>(BR)CBO</sub>	I <sub>C</sub> = 10μΑ, I <sub>E</sub> = 0		50			Vdc
Voltage	V (BR)CBU			50			vuc
Collector-Emitter Breakdown	V <sub>(BR)CEO</sub>	I <sub>C</sub> = 2.0mA, I <sub>B</sub> = 0		50			Vdc
Voltage NOTE3	1 (21)/020						
ON CHARACTERISTICS NOTE3		Г			[	[	[
			DTC114EE	35	60		
			DTC124EE	60	100		
			DTC144EE	80	140		
			DTC114YE	80	140		
			DTC114TE	160	350		
		V <sub>CE</sub> =10V,	DTC143TE	160	350		
DC Current Gain	hfe	I <sub>c</sub> =5.0mA	DTC123EE	8.0	15		
			DTC143EE	15	30		
			DTC143ZE	80	200		
			DTC124XE	80	150		
			DTC123JE	80	140		
			DTC115EE	80	150		
			DTC144WE	80	140		



# DTC114EE~DTC144WE

BIAS RESISTOR TRANSISTORS NPN SILICON WITH MONOLITHIC BIAS RESISTOR NETWORK

Parameter	Symbol	Conditions		Min.	Тур.	Max.	Unit
		$I_{\rm C}$ = 10mA, $I_{\rm B}$ = 0.3mA					
		I <sub>C</sub> = 10mA, I <sub>B</sub> = 5mA	DTC123EE				
Collector-Emitter Saturation			DTC143TE			0.05	) (dia
Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> = 10mA,	DTC114TE			0.25	Vdc
			DTC143EE				
		I <sub>B</sub> = 1mA	DTC143ZE				
			DTC124XE				
			DTC114EE			0.2	
			DTC124EE			0.2	
			DTC114YE			0.2	
			DTC114TE			0.2	
	Vol	V <sub>cc</sub> = 5.0V, V <sub>B</sub> = 2.5V, R <sub>L</sub> = 1.0kΩ	DTC143TE			0.2	
			DTC123EE			0.2	
			DTC143EE			0.2	
			DTC143ZE			0.2	
			DTC124XE			0.2	
Output Voltage (on)			DTC123JE			0.2	Vdc
		V <sub>CC</sub> = 5.0V,					
		V <sub>B</sub> = 3.5V,	DTC144EE			0.2	
		R <sub>L</sub> = 1.0kΩ					
		V <sub>CC</sub> = 5.0V,					
		V <sub>B</sub> = 5.5V,	DTC115EE			0.2	
		R∟ = 1.0kΩ					
		V <sub>CC</sub> = 5.0V,					
		V <sub>B</sub> = 4.0V,	DTC144WE			0.2	
		RL= 1.0kΩ					
		$V_{CC} = 5.0V, V_B = 0.5V,$					
		R <sub>L</sub> = 1.0kΩ					
Output Voltage (off)	Vau	V <sub>CC</sub> = 5.0V,	DTC143TE	4.9			Vdc
Output Voltage (off)	V <sub>он</sub>	$V_{CC} = 5.0V,$ $V_{B} = 0.25V,$	DTC143ZE	4.9			vuc
		v <sub>B</sub> = 0.25v, R <sub>L</sub> = 1.0kΩ	DTC114TE				
		nl = 1.0K12	DTC115EE				



BIAS RESISTOR TRANSISTORS NPN SILICON WITH MONOLITHIC BIAS RESISTOR NETWORK

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
	_	DTC114EE	7.0	10	13	
		DTC124EE	15.4	22	28.6	
		DTC144EE	32.9	47	61.1	
		DTC114YE	7.0	10	13	
		DTC114TE	7.0	10	13	
		DTC143TE	3.3	4.7	6.1	
Input Resistor	R1	DTC123EE	1.5	2.2	2.9	kΩ
		DTC143EE	3.3	4.7	6.1	
		DTC143ZE	3.3	4.7	6.1	
		DTC124XE	15.4	22	28.6	
		DTC123JE	1.54	2.2	2.86	
		DTC115EE	70	100	130	
		DTC144WE	32.9	47	61.1	
		DTC114EE/DTC124E/				
		DTC144EE/DTC115EE	0.8	1.0	1.2	
		DTC114YE	0.17	0.21	0.25	
		DTC143TE/DTC114TE	-	-	-	
Resistor Ratio	R1/R2	DTC123EE/DTC143EE	0.8	1.0	1.2	
		DTC143ZE	0.055	0.1	0.185	
		DTC124XE	0.38	0.47	0.56	
		DTC123JE	0.038	0.047	0.056	
		DTC144WE	1.7	2.1	2.6	

NOTE3: Pulse Test: Pulse Width < 300 us, Duty Cycle < 2.0%

## **RESISTOR VALUES**

Device	R1 (k)	R2 (k)
DTC114EE	10	10
DTC124EE	22	22
DTC144EE	47	47
DTC114YE	10	47
DTC114TE	10	œ
DTC143TE	4.7	œ
DTC123EE	2.2	2.2
DTC143EE	4.7	4.7
DTC143ZE	4.7	47
DTC124XE	22	47
DTC123JE	2.2	47
DTC115EE	100	100
DTC144WE	47	22



## TYPICAL CHARACTERISTICS

#### DTC114EE

Figure 1. V<sub>CE(sat)</sub> vs. IC

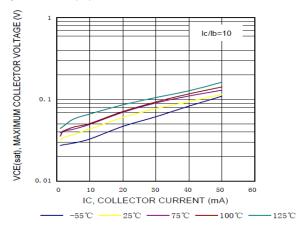


Figure 3. Output Capacitance

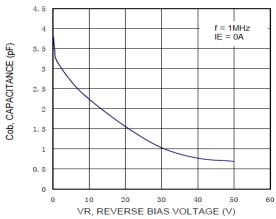
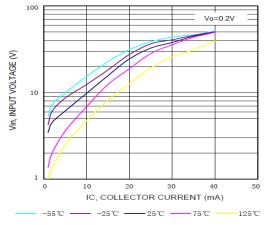


Figure 5. Input Voltage vs. Output Current



## Figure 2. DC Current Gain

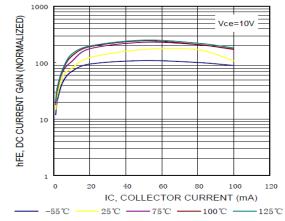
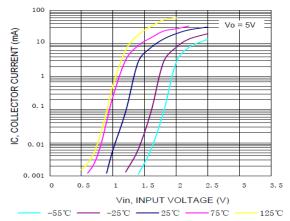


Figure 4. Output Current vs. Input Voltage





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### DTC115EE

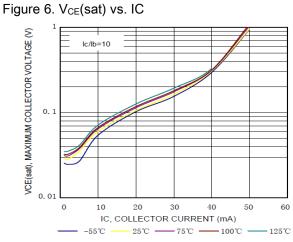


Figure 8. Output Capacitance

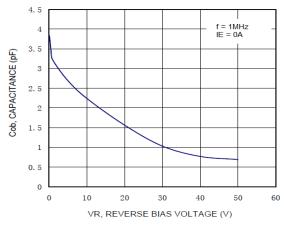


Figure 10. Input Voltage vs. Output Current

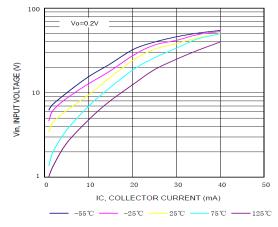


Figure 7. DC Current Gain

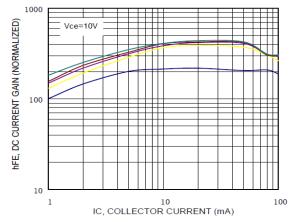
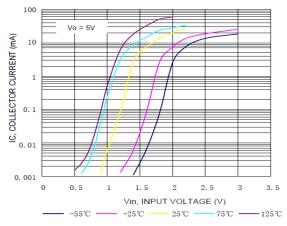


Figure 9. Output Current vs. Input Voltage





## TYPICAL APPLICATIONS FOR NPN BRTs

Figure 11. Level Shifter: Connects 12 To 24 Volt Circuits To Logic

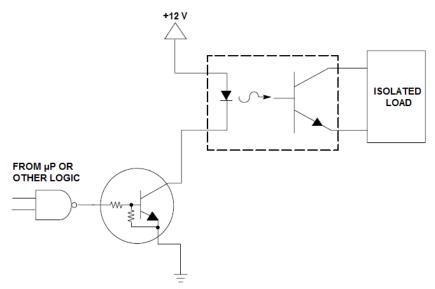
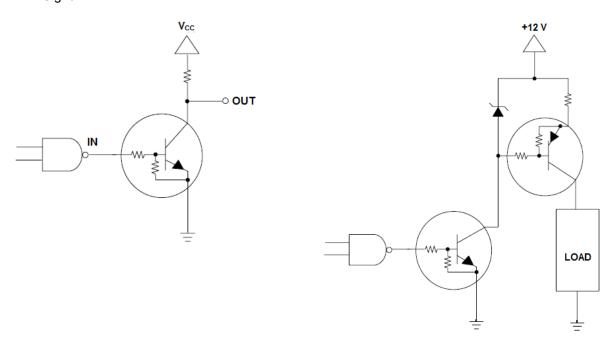


Figure 12. Open Collector Inverter: Inverts The Input Signal

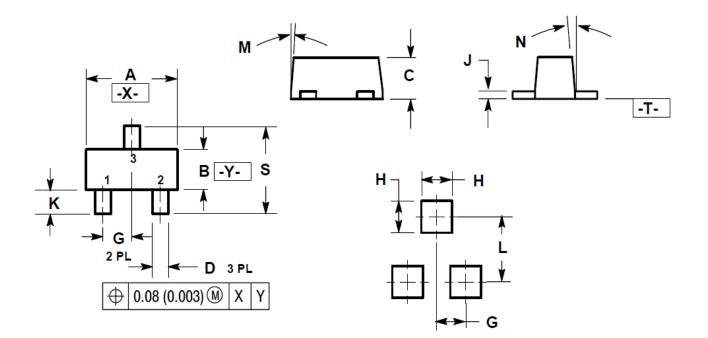
Figure 13. Inexpensive, Unregulated Current Source





# PACKAGE INFORMATION

Dimension in SC-89 Package (Unit: mm)



DIM	MILLIMETERS		INCHES		
DIM	MIN	MAX	MIN	MAX	
А	1.50	1.70	0.059	0.067	
В	0.75	0.95	0.030	0.040	
С	0.60	0.80	0.024	0.031	
D	0.23	0.33	0.009	0.013	
G	0.50 BSC		0.020 BSC		
Н	0.53	REF	0.02	1 REF	
J	0.10	0.20	0.004	0.008	
К	0.30	0.50	0.012	0.020	
L	1.10	REF	0.043 REF		
М	-	10°	_	10°	
N	-	10°	_	10°	
S	1.50	1.70	0.059	0.067	



## IMPORTANT NOTICE

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